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## 1. General description

NPN high-voltage low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9560Z

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- AEC-Q101 qualified

## 3. Applications

- Electronic ballast for fluorescent lighting
- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	600	V
I <sub>C</sub>	collector current		_	-	0.5	Α
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; $T_{amb}$ = 25 °C	70	135	-	





600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1—
3	Е	emitter		. 1
4	С	collector	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	3 sym016

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBHV8560Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV8560Z	HV856Z

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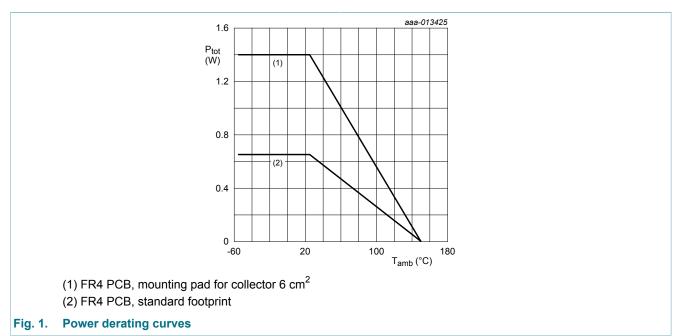
## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	600	V
$V_{CEO}$	collector-emitter voltage	open base		-	600	V
$V_{CESM}$	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	600	V
$V_{EBO}$	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.65	W
			<u>[2]</u>	-	1.4	W
$T_{j}$	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



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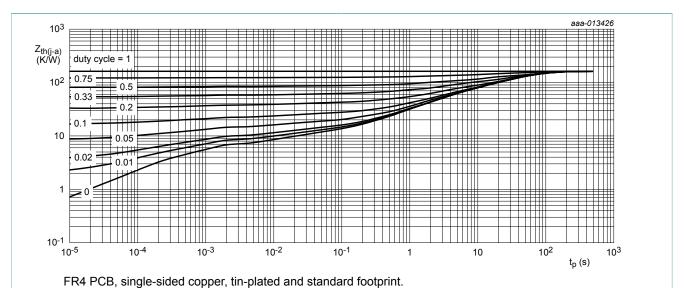
### Thermal characteristics

Table 6. Thermal characteristics

PBHV8560Z

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	190	K/W
			<u>[2]</u>	-	-	89	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 2.

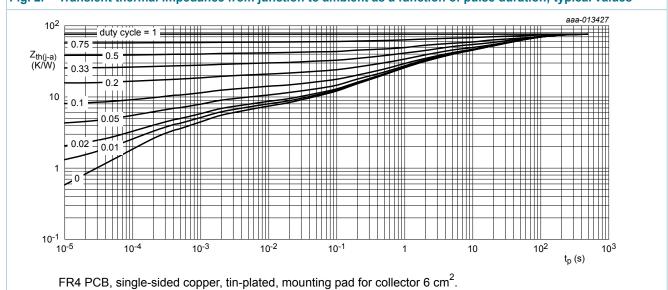


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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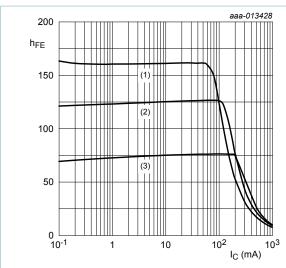
## 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Ісво	collector-base cut-off	V <sub>CB</sub> = 400 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 400 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	10	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 400 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C	70	135	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 100 mA; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	70	135	-	
V <sub>CEsat</sub> collector-emitter saturation voltage		$I_C$ = 50 mA; $I_B$ = 5 mA; $T_{amb}$ = 25 °C	-	50	100	mV
	saturation voltage	$I_{C}$ = 100 mA; $I_{B}$ = 20 mA; $t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	50	100	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_{C}$ = 50 mA; $I_{B}$ = 5 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	950	mV
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 20 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	7.5	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	710	-	pF

### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor



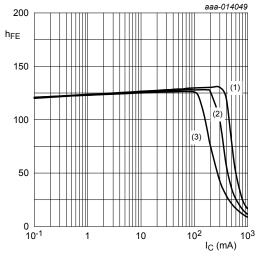
$$V_{CE} = 10 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55$$
 °C

Fig. 4. DC current gain as a function of collector current; typical values



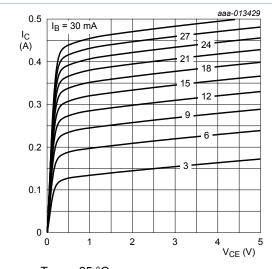
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$V_{CE} = 10 \text{ V}$$

(2) 
$$V_{CE} = 25 \text{ V}$$

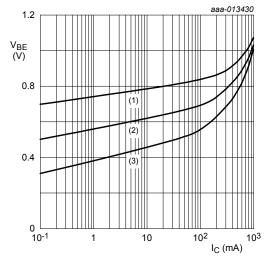
(3) 
$$V_{CE} = 50 \text{ V}$$

Fig. 5. DC current gain as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

Fig. 6. Collector current as a function of collectoremitter voltage; typical values



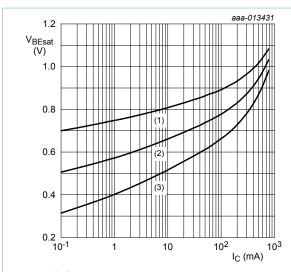
(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values

### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

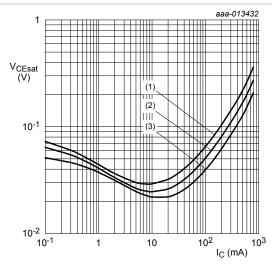


$$I_C/I_B = 5$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb}$$
= 100 °C



$$I_C/I_B = 5$$

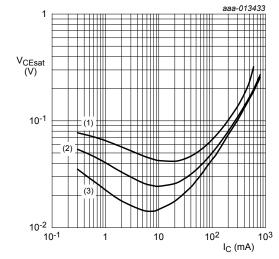
(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

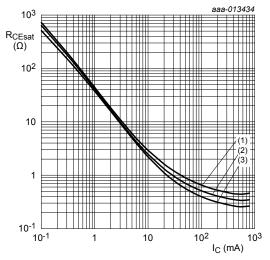


$$(1) I_{\rm C}/I_{\rm B} = 10$$

(2) 
$$I_C/I_B = 5$$

(3) 
$$I_C/I_B = 2.5$$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_C/I_B = 5$$

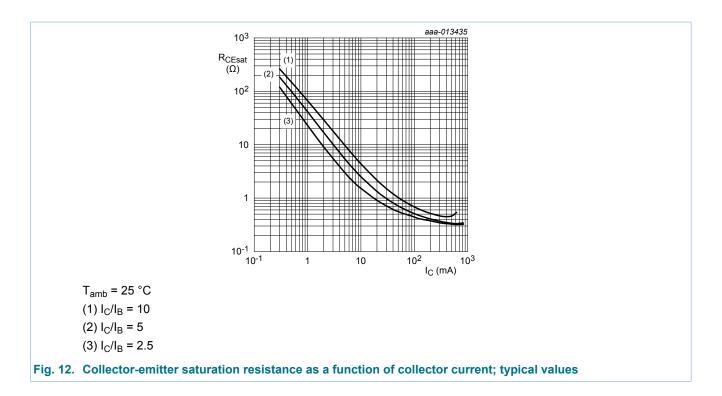
(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

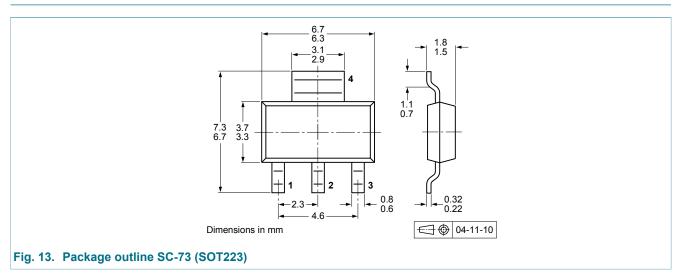


## 11. Test information

## 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline



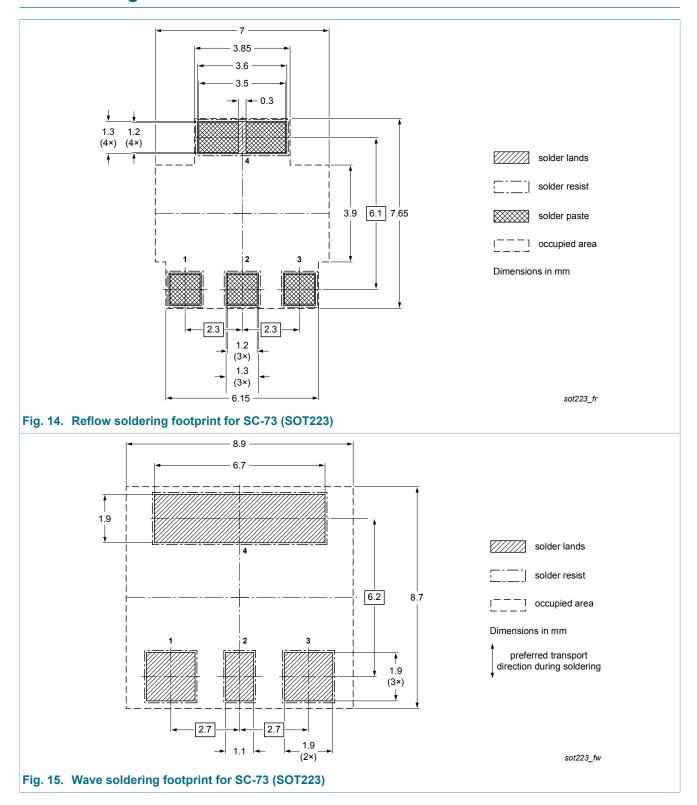
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## 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8560Z v.1	20150313	Product data sheet	-	-

#### 600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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